

Nikos Konofaos

List of Publications by Year in descending order

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92
papers

959
citations

471509

17
h-index

526287

27
g-index

93
all docs

93
docs citations

93
times ranked

939
citing authors

#	ARTICLE	IF	CITATIONS
1	Encoding Two-Qubit Logical States and Quantum Operations Using the Energy States of a Physical System. <i>Technologies</i> , 2022, 10, 1.	5.1	7
2	Simultaneous accessing of multiple SRAM subregions forming configurable and automatically generated memory fields. <i>International Journal of Circuit Theory and Applications</i> , 2021, 49, 2238-2254.	2.0	0
3	Noise investigation in a spin-based four-qubit GaAs block of self-assembled quantum dots. <i>AIP Advances</i> , 2021, 11, 065126.	1.3	0
4	A Model for Encoding Multiple Logical Qubit States into the Energy Eigenstates of a Transmon System. , 2021, , .		0
5	Quantum Pattern Recognition Method for Improving Pairwise Sequence Alignment. <i>Scientific Reports</i> , 2019, 9, 7226.	3.3	16
6	A Quantum Cellular Automata Type Architecture with Quantum Teleportation for Quantum Computing. <i>Entropy</i> , 2019, 21, 1235.	2.2	0
7	High-performance and energy-efficient 64-bit incrementer/decrementer using Multiple-Output Monotonic CMOS. <i>The Integration VLSI Journal</i> , 2018, 62, 270-281.	2.1	0
8	Low-power high-performance CMOS 5-bit compressor with 58 transistors. <i>Electronics Letters</i> , 2018, 54, 278-280.	1.0	16
9	Quantum recovery protocols for stabilizer codes: Deterministic Monte-Carlo simulation. <i>AIP Advances</i> , 2018, 8, .	1.3	0
10	Memory performance of MOS structure embedded with laser annealed gold NCs. <i>Solid-State Electronics</i> , 2018, 148, 63-69.	1.4	4
11	Improving the Sequence Alignment Method by Quantum Multi-Pattern Recognition. , 2018, , .		7
12	Design of Low-Power High-Performance 2 ⁿ -4 and 4 ⁿ -16 Mixed-Logic Line Decoders. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2017, 64, 176-180.	3.0	23
13	Ultra-low-power and compact 8-bit CMOS priority encoder. <i>International Journal of Electronics Letters</i> , 2017, 5, 272-278.	1.2	1
14	Quantum noise simulation: A software module for QuCirDET. , 2017, , .		0
15	PSK OFDM optical wireless communication systems with receiver's diversity over gamma-gamma turbulence channels and spatial jitter. , 2017, , .		3
16	Multi field SRAM access via intra-encoders and crossbar addressing scheme. , 2017, , .		2
17	High-Performance and Energy-Efficient 256-Bit CMOS Priority Encoder. , 2017, , .		5
18	Crossbar sector addressing scheme on SRAMs. , 2017, , .		1

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19	A VHDL implementation of the Hummingbird cryptographic algorithm. , 2017, , .		2
20	Design and implementation of quantum circuits for fault-tolerant architectures. , 2017, , .		0
21	Quantum Pattern Recognition for Local Sequence Alignment. , 2017, , .		2
22	QuCirDET: A design and simulation tool for quantum circuits. , 2016, , .		3
23	Low-power, high-performance 64-bit CMOS priority encoder using static-dynamic parallel architecture. , 2016, , .		9
24	Design and Simulation of 6T1R1W Cell Architectures in 32nm Technology. Journal of Engineering Science and Technology Review, 2016, 9, 145-149.	0.4	11
25	Organic photovoltaic performance improvement using atomic layer deposited ZnO electron-collecting layers. Solid-State Electronics, 2014, 101, 50-56.	1.4	8
26	On the Use of FDTD and Ray-Tracing Schemes in the Nanonetwork Environment. IEEE Communications Letters, 2014, 18, 1823-1826.	4.1	13
27	Formation of stoichiometric, sub-stoichiometric undoped and hydrogen doped tungsten oxide films, enabled by pulsed introduction of O ₂ or H ₂ during hot-wire vapor deposition. Thin Solid Films, 2013, 537, 124-130.	1.8	13
28	Highly porous tungsten oxides for electrochromic applications. Microelectronic Engineering, 2013, 111, 149-153.	2.4	18
29	Gate stack dielectric degradation of rare-earth oxides grown on high mobility Ge substrates. Journal of Applied Physics, 2012, 112, .	2.5	23
30	Hot-wire substoichiometric tungsten oxide films deposited in hydrogen environment with n-type conductivity. Journal Physics D: Applied Physics, 2012, 45, 445101.	2.8	5
31	Reduced transition metal oxides as electron injection layers in hybrid-PLEDs. Microelectronic Engineering, 2012, 90, 59-61.	2.4	9
32	Electrical reliability characteristics and dielectrics degradation in gate stacks (REO-HfO ₂) grown on the high mobility Ge substrates. , 2011, , .		0
33	Tungsten oxides as interfacial layers for improved performance in hybrid optoelectronic devices. Thin Solid Films, 2011, 519, 5748-5753.	1.8	38
34	Interface engineering for efficient organic optoelectronic devices using nanostructured transition metal oxides. , 2011, , .		0
35	Reduced molybdenum oxide as an efficient electron injection layer in polymer light-emitting diodes. Applied Physics Letters, 2011, 98, 123301.	3.3	49
36	A four base computational method for the implementation of a quantum computer using silicon devices: Circuit and simulation. Mathematical and Computer Modelling, 2010, 51, 144-149.	2.0	1

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37	Crystal quality and conductivity type of (002) ZnO films on (100) Si substrates for device applications. Solid-State Electronics, 2010, 54, 1150-1154.	1.4	12
38	A complementary single-electron 4-bit multiplexer. , 2010, , .		4
39	Estimation of a Target Position Based on Infrared Pattern Reception Quality. IETE Technical Review (Institution of Electronics and Telecommunication Engineers, India), 2010, 27, 36.	3.2	2
40	Crystal quality and conductivity type of epitaxial (002) ZnO films on (100) Si substrates for device applications. , 2009, , .		1
41	Developing quantum nanocomputing for pervasive health environments. , 2009, , .		0
42	Design, Simulation and Performance Evaluation of a NAND Based Single-electron 2-4 Decoder. , 2009, , .		7
43	Studying compatibilities between quantum cellular automata and Kane's semiconductor based quantum computer. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3865-3867.	0.8	0
44	Design, simulation and performance evaluation of a single-electron 2-4 decoder. Microelectronics Journal, 2008, 39, 1613-1621.	2.0	9
45	A methodology for the implementation of MOSFETs with a high-k dielectric gate material on the design of 90 nm technology circuits. International Journal of Electronics, 2008, 95, 333-349.	1.4	1
46	Design and Simulation of NAND Gates Made of Single Electron Devices. , 2008, , .		7
47	Using future position restriction rules for stabilizing the results of a noise-sensitive indoor localization system. Optical Engineering, 2007, 46, 067202.	1.0	7
48	Utilising noise effects on infrared pattern reception for position estimation on a grid plane. , 2007, , .		1
49	Implementation of a Hadamard Gate Using Laser Light on a Phosphorus Doped Si Device. AIP Conference Proceedings, 2007, , .	0.4	0
50	Rare earth oxides as high-k dielectrics for Ge based MOS devices: An electrical study of Pt/Gd ₂ O ₃ /Ge capacitors. Solid-State Electronics, 2007, 51, 164-169.	1.4	23
51	The peak and average temperature in a self-heated GaN HFET. Solid-State Electronics, 2007, 51, 142-146.	1.4	2
52	A wireless infrared sensor network for the estimation of the position and orientation of a moving target. , 2007, , .		0
53	Target Localization Utilizing the Success Rate in Infrared Pattern Recognition. IEEE Sensors Journal, 2006, 6, 1355-1364.	4.7	19
54	Utilizing infrared pattern recognition features for indoor localization validated by future position restrictions. , 2006, , .		1

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55	<title>Design and simulation of an embedded DRAM cell made up of MOSFETs having alternative gate dielectrics</title>. , 2005, , .		2
56	Temperature dependence of the electrical properties of MOS devices constructed by sol gel deposited BaTiO ₃ films on p-Si. Journal of Physics: Conference Series, 2005, 10, 49-52.	0.4	0
57	Defect related effects on the reliability and performance of an embedded DRAM cell designed with MOSFETs with alternative gate dielectrics. Journal of Physics: Conference Series, 2005, 10, 365-368.	0.4	3
58	An electrical, optical and electron paramagnetic resonance study of room temperature deposited CN _x films on Si. Thin Solid Films, 2005, 482, 270-274.	1.8	0
59	Characterization of physical and electrical properties of BaTiO ₃ films deposited on p-Si by modified polymeric precursors. Journal of Electronic Materials, 2005, 34, 1259-1263.	2.2	3
60	A New Concept On A Quantum Computer Based On Shockley-Read-Hall Recombination Statistics In Microelectronic Devices. AIP Conference Proceedings, 2005, , .	0.4	0
61	A quantum computer based on recombination processes in microelectronic devices. Journal of Physics: Conference Series, 2005, 10, 85-88.	0.4	0
62	A Quantum Computer Architecture Based on Semiconductor Recombination Statistics. Lecture Notes in Computer Science, 2005, , 582-588.	1.3	1
63	Properties of Al ⁺ SrTiO ₃ Capacitors for Microelectronic Device Applications. IEEE Transactions on Electron Devices, 2004, 51, 1202-1205.	3.0	6
64	Dielectric properties of CVD grown SiON thin films on Si for MOS microelectronic devices. Semiconductor Science and Technology, 2004, 19, 50-53.	2.0	29
65	Electrical characterisation of SiON/n-Si structures for MOS VLSI electronics. Microelectronics Journal, 2004, 35, 421-425.	2.0	74
66	Dielectric properties and electronic transitions of porous and nanostructured cerium oxide films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 69-73.	3.5	42
67	Electrical characterization of the SiON/Si interface for applications on optical and MOS devices. Semiconductor Science and Technology, 2003, 18, 56-59.	2.0	41
68	Electrical properties of carbon nitride films on silicon. Journal of Applied Physics, 2002, 91, 9915.	2.5	7
69	Electrical characterisation of SrTiO ₃ /Si interfaces. Journal of Non-Crystalline Solids, 2002, 303, 185-189.	3.1	14
70	The effects of interface and bulk defects on the electrical performance of amorphous carbon/silicon heterojunctions. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 379-383.	3.5	7
71	Characteristics of SrTiO ₃ thin films deposited on Si by rf magnetron sputtering at various substrate temperatures. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 2002, 82, 891-903.	0.6	6
72	Temperature dependence of the barrier at the tetrahedral amorphous carbon-silicon interface. Semiconductor Science and Technology, 2001, 16, 474-477.	2.0	2

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73	New evidence on the relation between tunnelling and trap density at insulator/semiconductor interfaces. <i>Semiconductor Science and Technology</i> , 2001, 16, 733-738.	2.0	7
74	Electrical properties of SrTiO ₃ thin films on Si deposited by magnetron sputtering at low temperature. <i>Applied Physics Letters</i> , 2001, 79, 1513-1515.	3.3	53
75	Characterization of BaTiO ₃ thin films on p-Si. <i>Materials Science in Semiconductor Processing</i> , 2001, 4, 305-307.	4.0	10
76	Electrical characterization and carrier transport mechanisms of GaAs p/i/n devices for photovoltaic applications. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2001, 80, 152-155.	3.5	4
77	Electrical characterization of TiN/a-C/Si devices grown by magnetron sputtering at room temperature. <i>Applied Physics Letters</i> , 2001, 78, 1682-1684.	3.3	9
78	Charge carrier response time in sputtered a-C/n-Si heterojunctions. <i>Applied Physics Letters</i> , 2001, 79, 2381-2383.	3.3	15
79	Nitrogen induced states at the CN _x /Si interface. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000, 71, 315-320.	3.5	3
80	Characterisation of the BaTiO ₃ /p-Si interface and applications. <i>Applied Surface Science</i> , 2000, 166, 504-507.	6.1	25
81	Characterization of magnetron sputtering deposited thin films of TiN for use as a metal electrode on TiN/SiO ₂ /Si metal-oxide-semiconductor devices. <i>Journal of Applied Physics</i> , 2000, 88, 7192-7196.	2.5	19
82	Properties of barium titanate (BaTiO ₃) thin films grown on silicon by rf magnetron sputtering. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 2000, 80, 395-407.	0.6	22
83	Effect of the layered structure on the electronic properties of amorphous carbon films on n-Si. <i>Journal of Applied Physics</i> , 1999, 86, 4446-4451.	2.5	10
84	Electrical behaviour of metal/a-C/Si and metal/CN/Si devices. <i>Carbon</i> , 1999, 37, 871-876.	10.3	10
85	Electronic transport phenomena in devices containing amorphous diamond-like films on silicon. <i>Solid State Communications</i> , 1998, 105, 257-261.	1.9	4
86	Device characterization for amorphous diamond-like carbon-silicon heterojunctions. <i>Journal of Applied Physics</i> , 1998, 84, 4634-4636.	2.5	13
87	Characterization of heterojunction devices constructed by amorphous diamondlike films on silicon. <i>Journal of Applied Physics</i> , 1997, 81, 6238-6245.	2.5	36
88	Properties and density of states of the interface between silicon and carbon films rich in sp ³ bonds. <i>Journal of Applied Physics</i> , 1997, 82, 5017-5020.	2.5	25
89	Characterisation of the Interface States between Amorphous Diamond-Like Carbon Films and (100) Silicon. <i>Physica Status Solidi A</i> , 1997, 161, 111-123.	1.7	41
90	Conductance technique measurements of the density of states between Si and ZnS grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 1993, 74, 397-401.	2.5	6

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91	Amorphous diamondlike carbon-silicon heterojunction devices formed by ion implantation. Applied Physics Letters, 1992, 61, 2805-2807.	3.3	25
92	Modeling and Simulation of Submicron MOSFETs with Alternative Gate Dielectrics for DRAM Cells. , 0, , .		0